

100V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
100V	$17.4 \text{m}\Omega @ V_{GS} = 10V$	59A
	$30.3 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	45A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

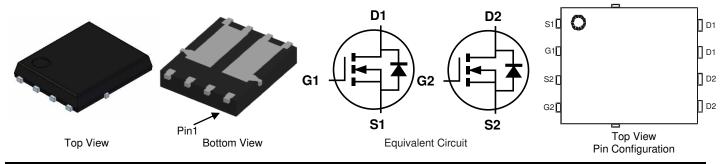
- Synchronous Rectifier
- DC-DC Converters
- Primary Side Switching

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH10H017LPDQ</u>)

Mechanical Data

- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging	
DMTH10H017LPD-13	PowerDI5060-8 (Type E)	2500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃ | |= Manufacturer's Marking H10H017LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

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April 2019



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$		I _D	59 42	А
Maximum Body Diode Forward Current (Note 6)		Is	60	Α
Pulsed Drain Current (10µs Pulse, T _C = +25°C, Package Limited)		I_{DM}	236	Α
Pulsed Body Diode Forward Current (10µs Pulse, T _C = +25°C, Package Li	I _{SM}	236	Α	
Avalanche Current, L = 3mH (Note 9)	Ias	10	Α	
Avalanche Energy, L = 3mH (Note 9)	E _{AS}	150	mJ	
Avalanche Current, L = 1mH (Note 9)		las	10	Α
Avalanche Energy, L = 1mH (Note 9)		Eas	50	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation	$T_A = +25$ °C	P _D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	56	°C/W
Total Power Dissipation	$T_C = +25^{\circ}C$	P _D	93	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	1.6	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol Min Typ Max Unit		Test Condition				
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV_{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	נ	_	13.7	17.4	mΩ	V _{GS} = 10V, I _D = 17A	
Static Dialii-Source Oil-nesistance	R _{DS(ON)}	_	23.8	30.3	11122	V _{GS} = 4.5V, I _D = 10A	
Diode Forward Voltage	V_{SD}		_	1.3	V	V _{GS} = 0V, I _S = 17A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	1986	_		V _{DS} = 50V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	333	_	pF		
Reverse Transfer Capacitance	C_{rss}	_	20	_			
Gate Resistance	R _G	_	1.17	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	14.4	_			
Total Gate Charge (V _{GS} = 10V)	Q_g	_	28.6	_	nC	$V_{DS} = 50V, I_D = 20A$	
Gate-Source Charge	Q _{gs}	_	5.2	_	110		
Gate-Drain Charge	Q _{gd}	_	8.2	_			
Turn-On Delay Time	t _{D(ON)}	_	9.8	_		V _{DD} = 50V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	_	16.3	_			
Turn-Off Delay Time	t _{D(OFF)}		32.6	_	ns	$R_G = 11\Omega$, $I_D = 20A$	
Turn-Off Fall Time	t _F		21.6	_			
Body Diode Reverse Recovery Time	t _{RR}	_	40.6	_	ns	I _F = 17A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q_{RR}	_	58.1	_	nC	I _F = 17A, di/dt = 100A/µs	

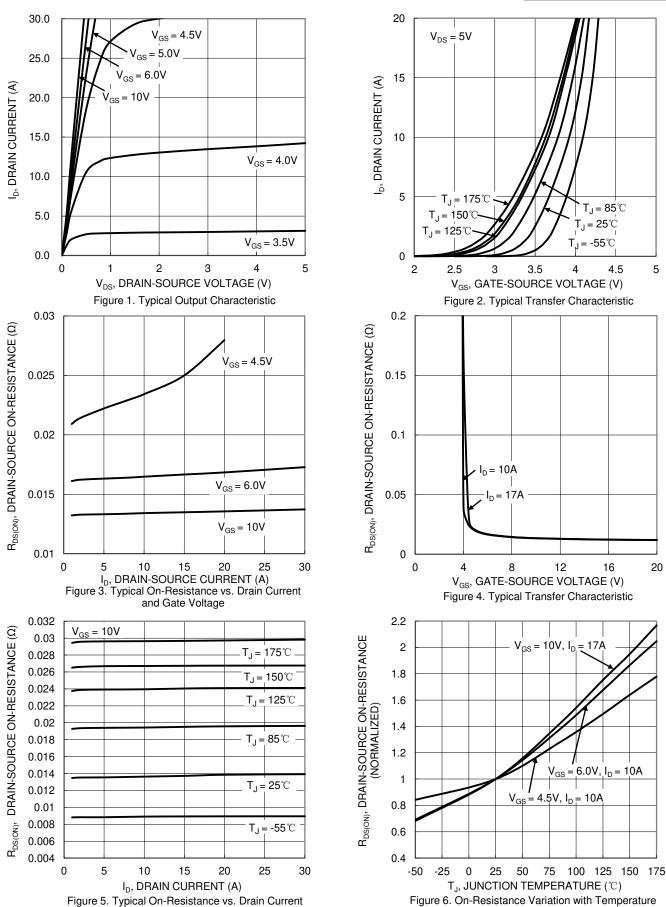
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Thermal resistance from junction to solder point (on the exposed drain pin).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

- 9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_{J} = +25°C.







and Temperature





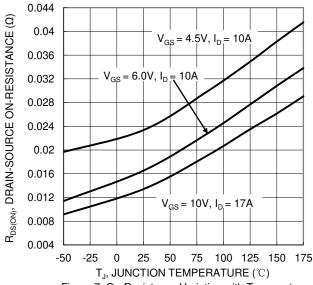
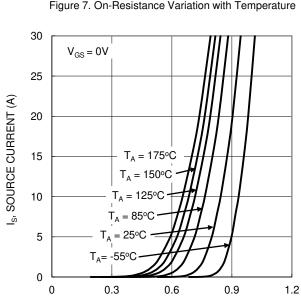


Figure 7. On-Resistance Variation with Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

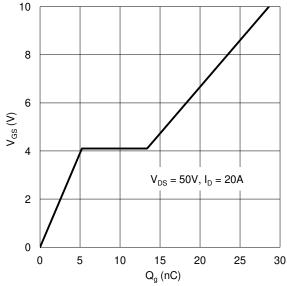


Figure 11. Gate Charge

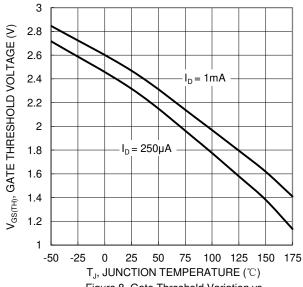


Figure 8. Gate Threshold Variation vs. JunctionTemperature

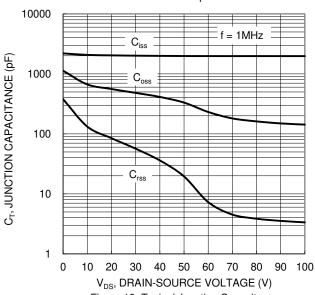


Figure 10. Typical Junction Capacitance

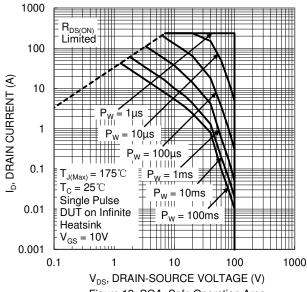
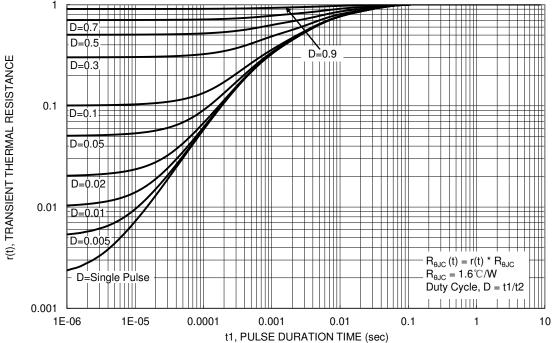


Figure 12. SOA, Safe Operation Area



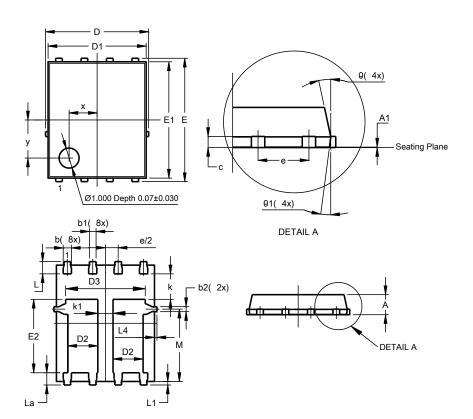




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type E)

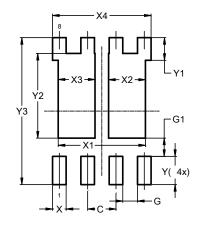


PowerDI5060-8 (Type E)						
Dim	Min Max		Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
С	0.23	0.33	0.277			
D	5	5.15 BSC				
D1	4.85	4.95	4.90			
D2	1.40	1.60	1.50			
D3	-	-	3.98			
Е		.15 BS0)			
E1	5.75	5.85	5.80			
E2	3.56	3.76	3.66			
е	1	.27BSC				
k	-	-	1.27			
k1	0.56	-	-			
L	0.51	0.71	0.61			
La	0.51	0.71	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
М	3.50	3.71	3.605			
X	-	-	1.400			
у	'		1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type E)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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